

Transistor Level Modeling for Analog/RF IC Design

Edited by

WLADYSLAW GRABINSKI

Geneva Modeling Center, Freescale, Switzerland

BART NAUWELAERS

K.U. Leuven, Belgium

and

DOMINIQUE SCHREURS

K.U. Leuven, Belgium

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TABLE OF CONTENTS

Foreword <i>Hiroshi Iwai</i>	vii
Introduction <i>Wladek Grabinski, Bart Nauwelaers and Dominique Schreurs</i>	ix
1 2/3-D process and device simulation. An effective tool for better understanding of internal behavior of semiconductor structures <i>Daniel Donoval, Andrej Vrbicky, Ales Chvala, and Peter Beno</i>	1
2 PSP: An advanced surface-potential-based MOSFET model <i>R. van Langevelde, and G. Gildenblat</i>	29
3 EKV3.0: An advanced charge based MOS transistor model. A design-oriented MOS transistor compact model for next generation CMOS <i>Matthias Bucher, Antonios Bazigos, François Krummenacher, Jean-Micehl Sallese, and ChristianENZ</i>	67
4 Modelling using high-frequency measurements <i>Dominique Schreurs</i>	97

5		
Empirical FET models		121
<i>Iltcho Angelov</i>		
6		
Modeling the SOI MOSFET nonlinearities. An empirical approach		157
<i>B. Parvais, A. Siligaris</i>		
7		
Circuit level RF modeling and design		181
<i>Nobuyuki Itoh</i>		
8		
On incorporating parasitic quantum effects in classical circuit simulations		209
<i>Frank Felgenhauer, Maik Begoin and Wolfgang Mathis</i>		
9		
Compact modeling of the MOSFET in VHDL-AMS		243
<i>Christophe Lallement, François Pêcheux, Alain Vachoux and Fabien Prégaldiny</i>		
10		
Compact modeling in Verilog-A		271
<i>Boris Troyanovsky, Patrick O'Halloran and Marek Mierzwinski</i>		
Index		293